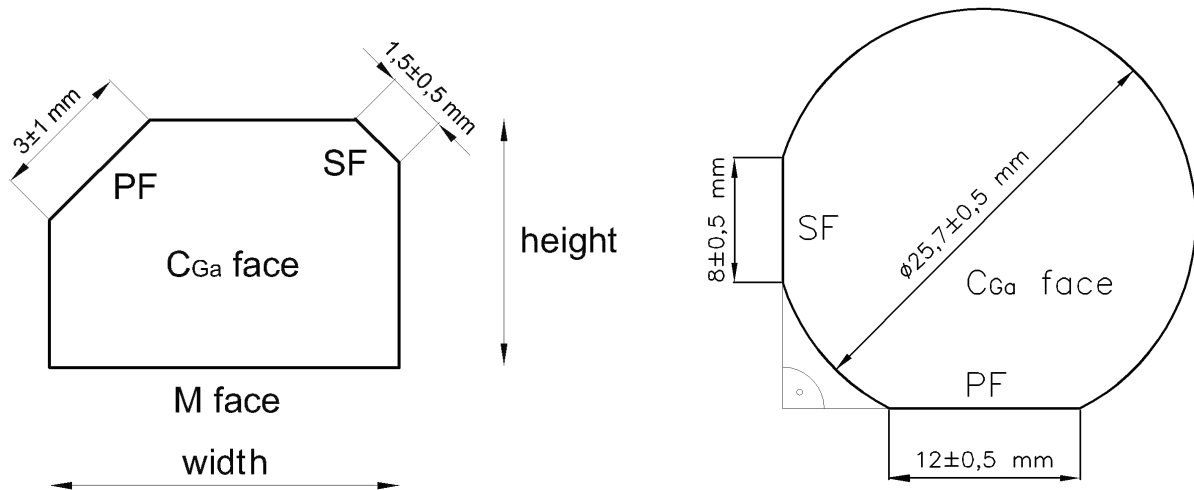


## C-plane GaN Substrates

Features	Units	Conductivity		
		n-type	p-type	SI
Carrier concentration	cm <sup>-3</sup>	~ 10 <sup>19</sup>	~ 10 <sup>18</sup>	-
Resistivity	Ω·cm	10 <sup>-3</sup> – 10 <sup>-2</sup>	10 <sup>2</sup> - 10 <sup>3</sup>	10 <sup>9</sup> - 10 <sup>12</sup>
Mobility	cm <sup>2</sup> /V·s	~ 150	-	-
Thickness	μm	≥ 300	≥ 300	≥ 300
Total thickness variation (TTV)	μm	< 40	< 40	< 40
Bow	μm	≤ 10	≤ 10	≤ 10
FWHM of X-ray rocking curve, epi-ready surface at 100 μm x 100 μm slit)	arcsec	~ 20	~ 20	~ 20
Dislocation density	cm <sup>-2</sup>	< 10 <sup>5</sup>	< 10 <sup>5</sup>	< 10 <sup>5</sup>
Misorientation	deg	On demand		
Surface finishing		As cut / ground Roughly polished Optically polished (RMS < 3 nm) Epi-ready (RMS < 0.5 nm)		
Available sizes		10x10 mm, 1", 1.5"		
Packaging		Separate single wafer container		
Special Order Option		Please, contact Sales Department		



Rectangular and 1" round substrates